

N-Channel Enhancement-Mode MOSFET

DESIGNED FOR:

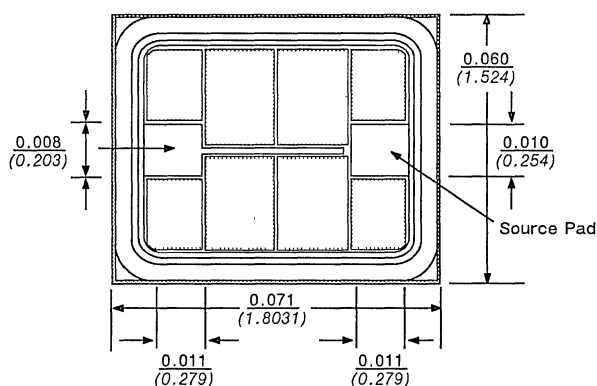
- Switching
- Amplification

FEATURES

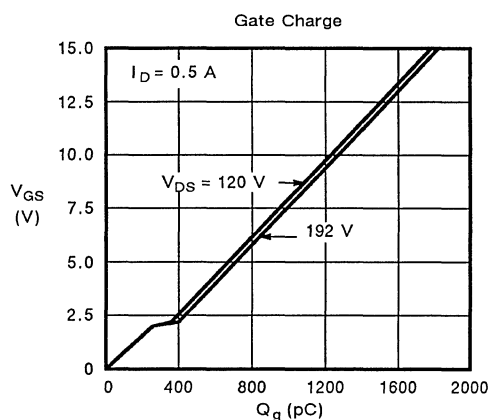
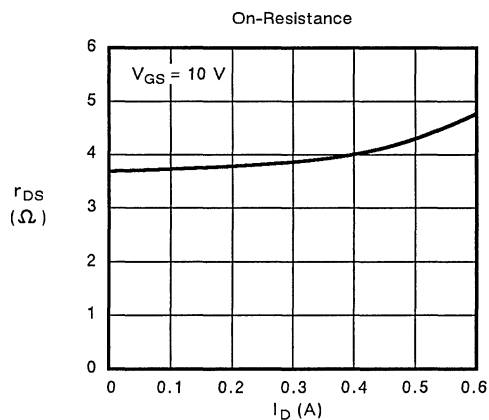
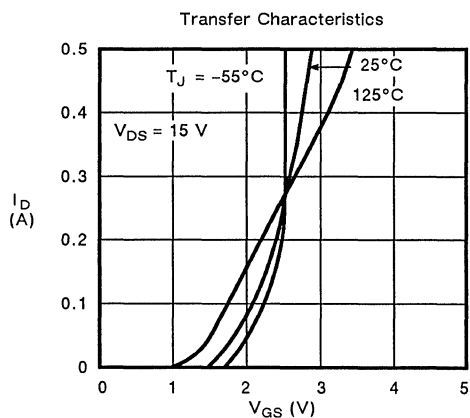
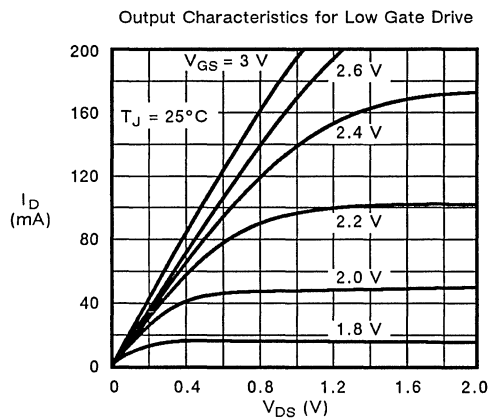
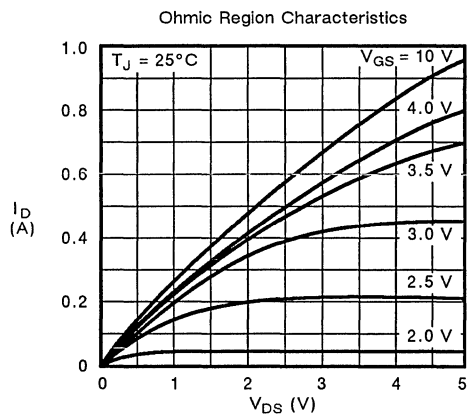
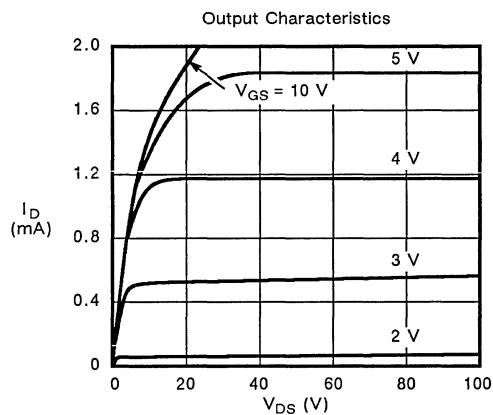
- High Breakdown > 240 V
- Low $r_{DS(on)} < 6 \Omega$

TYPE	PACKAGE	DEVICE
Single	TO-205AD	• VN1706B, VN2406B
	TO-220	• VN1706D, VN2406D
	TO-92	• VN1706L, VN2406L
	TO-237	• VN1706M, VN1710M, VN2406M
	Chip	• Available as above specifications

GEOMETRY DIAGRAM

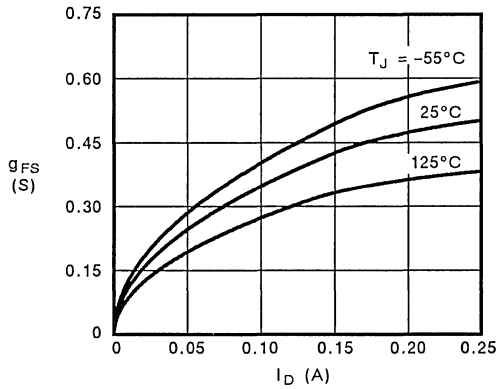


TYPICAL CHARACTERISTICS

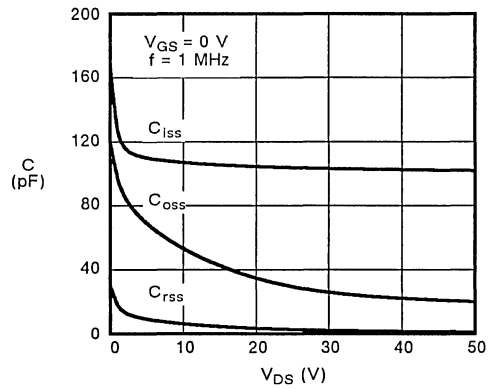


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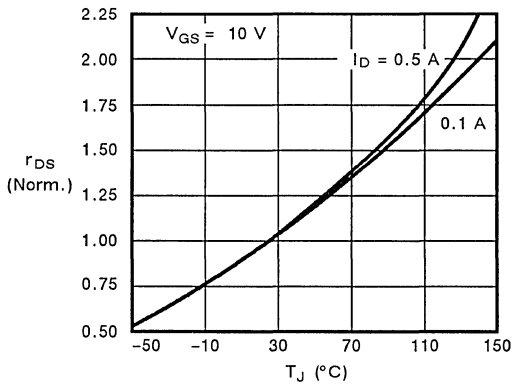
Transconductance



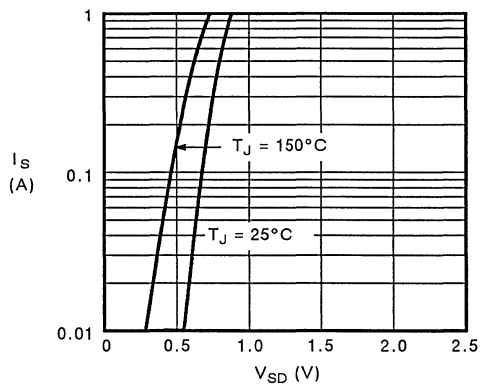
Capacitance



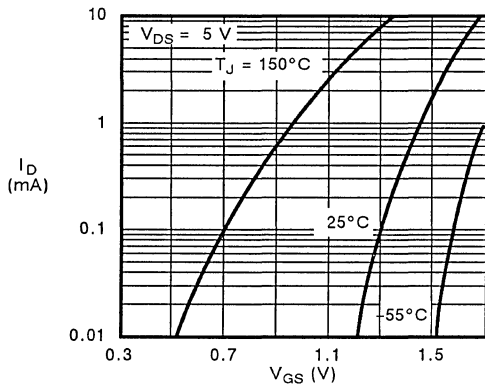
On-Resistance vs. Junction Temperature



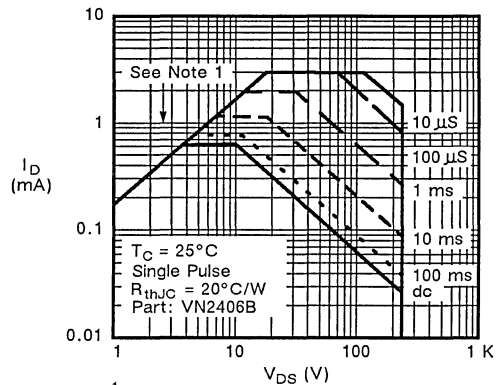
Source-Drain Diode Forward Voltage



Threshold Region

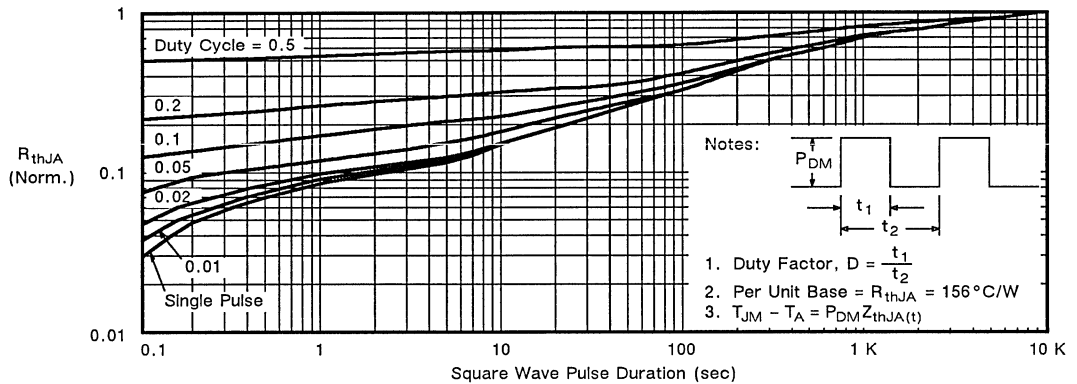


Safe Operating Area

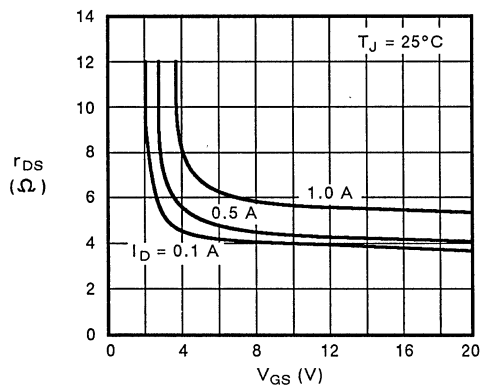


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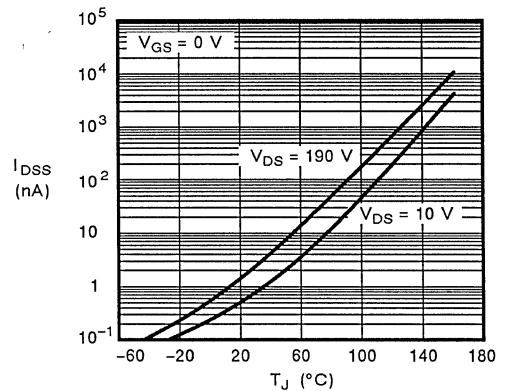
Normalized Effective Transient Thermal Impedance, Junction-to-Ambient (TO-92)



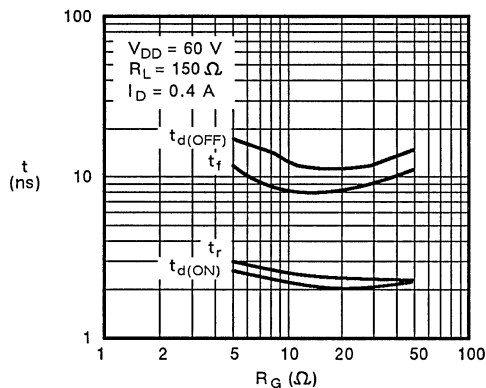
On-Resistance vs. Gate to Source Voltage



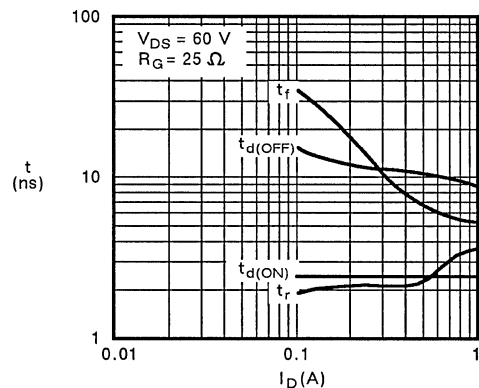
Off State Current



Drive Resistance Effects on Switching

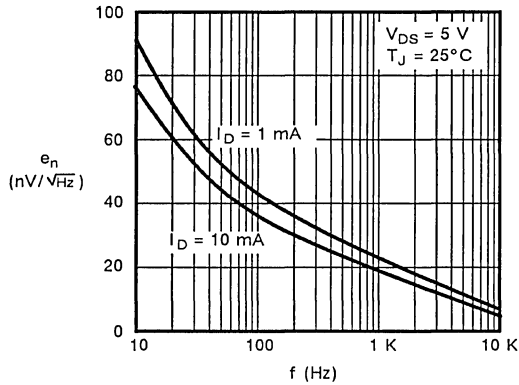


Load Condition Effects on Switching

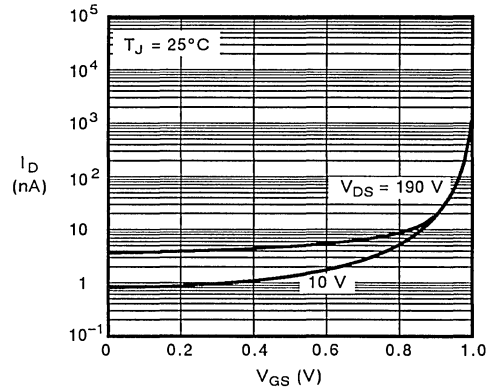


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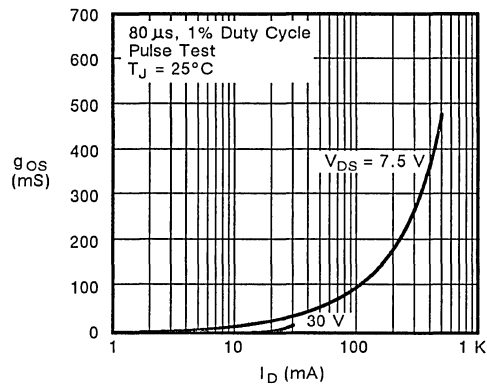
Equivalent Input Noise Voltage vs. Frequency



Body Drain Leakage Current



Output Conductance vs. Drain Current



Transient Thermal Response (TO-205AD)

